

IN THE CLAIMS

Claim 1-10 (Cancelled).

11 (Currently Amended). A semiconductor structure comprising:
a gate; and
an implanted region including both germanium and P-type impurities wherein the ratio of germanium to P-type impurities is greater than one.

Claim 12 (Canceled).

13 (Currently Amended). The structure of claim 11 ~~12~~ wherein the ratio of germanium to P-type impurities is approximately four to one.

14 (Original). The structure of claim 13 wherein said P-type impurities are boron impurities.

15 (Original). The structure of claim 11 wherein said germanium is implanted to a depth greater than about 150 Angstroms.

16 (Original). The structure of claim 11 wherein said implanted region is a source/drain extension.

17 (Original). The structure of claim 16 wherein said implanted region is a strained source/drain junction.

18 (Original). The structure of claim 11 including a polysilicon gate.

19 (Original). The structure of claim 18 including a polysilicon gate with side wall spacers.

20 (Original). An integrated circuit comprising:
a semiconductor structure;
a gate formed on said semiconductor structure; and
a source and a drain region, said source and drain region including both germanium and a P-type impurity, said source and drain region being strained.

21 (Original). The circuit of claim 20 wherein the ratio of germanium to P-type impurities is greater than one to one.

22 (Original). The circuit of claim 20 wherein the ratio of germanium to P-type impurities is approximately four to one.

23 (Original). The circuit of claim 20 wherein said P-type impurities are boron impurities.

24 (Original). The circuit of claim 20 wherein said source/drain region that includes both boron and germanium is a source/drain extension.